

**SCALABLE FLASH/NV STRUCTURES AND DEVICES
WITH EXTENDED ENDURANCE**

Abstract of the Disclosure

5 Devices and methods are provided with respect to a gate stack for a
nonvolatile structure. According to one aspect, a gate stack is provided. One
embodiment of the gate stack includes a tunnel medium, a high K charge blocking
and charge storing medium, and an injector medium. The high K charge blocking
and charge storing medium is disposed on the tunnel medium. The injector medium
10 is operably disposed with respect to the tunnel medium and the high K charge
blocking and charge storing medium to provide charge transport by enhanced
tunneling. According to one embodiment, the injector medium is disposed on the
high K charge blocking and charge storing medium. According to one embodiment,
the tunnel medium is disposed on the injector medium. Other aspects and
15 embodiments are provided herein.

"Express Mail" mailing label number: EL873859928US

Date of Deposit: August 30, 2001

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